

Amendments to the Claims

This listing of the claims will replace all prior versions and listings of the claims in the application.

Listing of Claims:

1. (original): A high density plasma oxide film deposition apparatus comprising:
 - a chuck having an upper surface onto which a semiconductor substrate is to be loaded, and an outer peripheral side wall;
 - an upper electrode confronting and spaced from the upper surface of said chuck; and
 - a guide ring extending around said chuck, said guide ring comprising a first annular portion having an inner peripheral side wall surrounding the outer peripheral side wall of said chuck, a second annular portion extending upwardly from an outer peripheral region of said first annular portion and having an inner peripheral side wall disposed radially outwardly of the inner peripheral side wall of said first annular portion, and at least three protrusions extending from the inner peripheral side wall of said second annular portion toward the inner peripheral side wall of said first annular portion, said protrusions being spaced from one another in the circumferential direction of said second annular portion, and said protrusions having terminal ends remote from the inner peripheral side wall of said second annular portion and situated radially outwardly of the inner peripheral side wall of said first annular portion, said terminal ends lying along a circle whose diameter is greater than the inner diameter of said first annular portion.
2. (original): The high density plasma oxide film deposition apparatus of claim 1, wherein said chuck is an electrostatic chuck.
3. (original): The high density plasma oxide film deposition apparatus of

claim 2, wherein the apparatus further comprises a first power source connected to said upper electrode, and a second power source connected to said electrostatic chuck.

4. (original): The high density plasma oxide film deposition apparatus of claim 3, wherein said first power source has a bias and a radio frequency within ranges of 2000 ~ 3000 Watts and 1.8 ~ 2.2 MHz, respectively, and said second power source has a bias and a radio frequency within ranges of 2000 ~ 3000 Watts and 13.37 ~ 13.64 MHz, respectively.

5. (original): The high density plasma oxide film deposition apparatus of claim 3, wherein said first power source has a bias and a radio frequency within ranges of 2000 ~ 3000 Watts and 13.37 ~ 13.64 MHz, respectively, and said second power source has a bias and a radio frequency within ranges of 2000 ~ 3000 Watts and 1.8 ~ 2.2 MHz, respectively.

6. (original): The high density plasma oxide film deposition apparatus of claim 1, wherein the apparatus further comprises a chamber within which the chuck, the upper electrode and the guide ring are disposed.

7. (original): The high density plasma oxide film deposition apparatus of claim 1, wherein the first and the second annular portions of said guide ring are concentric.

8. (original): The high density plasma oxide film deposition apparatus of claim 7, wherein said protrusions are spaced equidistantly from each other in the circumferential direction of said second annular portion.

9 – 19. (cancelled)